

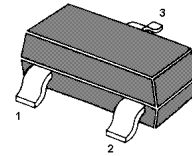
**PNP Silicon Epitaxial Planar Transistor**

For switching and general purpose applications.

The transistor is subdivided into three groups O, Y and GR, according to its DC current gain.

**Features**

 Excellent  $h_{FE}$  linearity:

 $h_{FE}=25(\text{min})$  at  $V_{CE}=-6V$ ,  $I_C=-400\text{mA}$ 

 1. Base 2. Emitter 3. Collector  
 SOT-23 Plastic Package

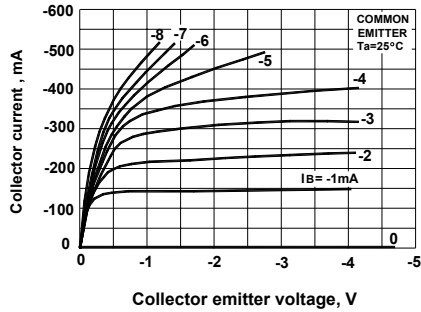
**Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )**

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	35	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Base Current	$-I_B$	50	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	-55 to +150	$^\circ\text{C}$

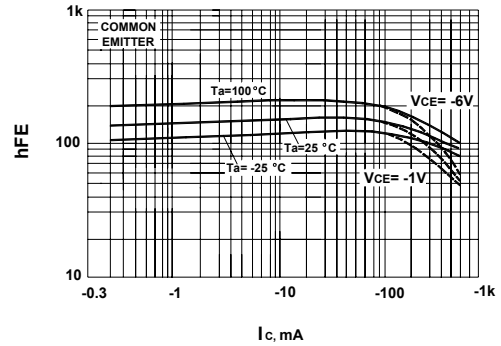
**Characteristics at  $T_{amb}=25\text{ }^{\circ}\text{C}$** 

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=1\text{V}$ , $-I_C=100\text{mA}$					
Current Gain Group O	$h_{FE}$	70	-	140	-
Y	$h_{FE}$	120	-	240	-
GR	$h_{FE}$	200	-	400	-
at $-V_{CE}=6\text{V}$ , $-I_C=400\text{mA}$					
O	$h_{FE}$	25	-	-	-
Y	$h_{FE}$	40	-	-	-
Collector Cutoff Current at $-V_{CB}=35\text{V}$	$-I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	$\mu\text{A}$
Collector Saturation Voltage at $-I_C=100\text{mA}$ , $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	-	0.25	V
Base Emitter Voltage at $-V_{CE}=1\text{V}$ , $-I_C=100\text{mA}$	$-V_{BE}$	-	-	1	V
Transition Frequency at $-V_{CE}=6\text{V}$ , $-I_C=20\text{mA}$	$f_T$	-	200	-	MHz
Collector Output Capacitance at $-V_{CB}=6\text{V}$ , $f=1\text{MHz}$	$C_{ob}$	-	13	-	pF

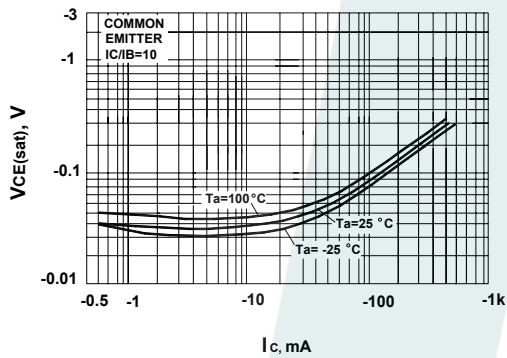
**Ic - Vce(Low Voltage Region)**



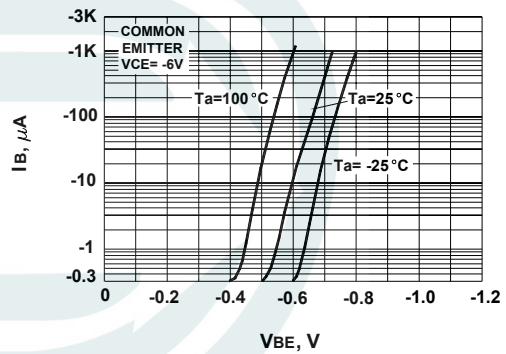
**hFE - Ic**



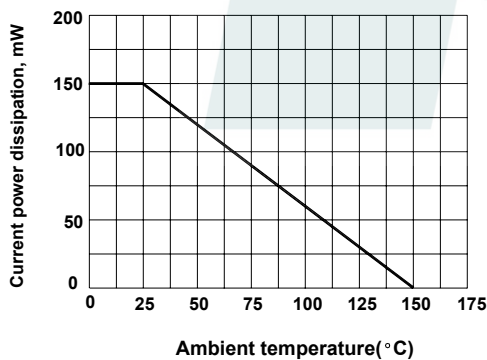
**Vce(sat) - Ic**



**IB - VBE**



**Pc - Ta**



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